

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Masahiro SAKURADA et al.

Application No.: New U.S. Patent Application

Filed: June 14, 2005

Docket No.: 124231

For: METHOD OF PRODUCING P-DOPED SILICON SINGLE CRYSTAL AND P-DOPED N-TYPE SILICON SINGLE CRYSTAL WAFER

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Pursuant to 37 CFR §1.56, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO-1449. Unless otherwise indicated herein, one copy of each reference is attached. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

- ☒ 1. This Information Disclosure Statement is being filed (a) within three months of the U.S. filing date of this non-CPA application, OR (b) before the mailing date of a first Office Action on the merits in the present application. No certification or fee is required.
- ☒ 2. Relevance of the non-English language references 2-4 are discussed in the present specification.
- ☒ 3. The reference 1 was cited in an International Search Report. An English language version of an International Search Report is attached for the Examiner's information.
- ☒ 4. English language Abstracts of the non-English language references 1-2 are attached hereto.

107538878

JC17 Rec'd PCT/PTO 14 JUN 2005



5. A computer-generated English language translation of the following Japanese Patent Publication has been obtained from the website of the Japanese Patent Office (<http://www.jpo.go.jp>), and is attached, but has not been reviewed for accuracy. See References 1-2.

Respectfully submitted,

William P. Berridge
Registration No. 30,024

Eric D. Morehouse
Registration No. 38,565

WPB:EDM/mps

Date: June 14, 2005

OLIFF & BERRIDGE, PLC
P.O. Box 19928
Alexandria, Virginia 22320
Telephone: (703) 836-6400

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Form PTO-1449 (REV. 8-83)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 124231		APPLICATION NO. New U.S. National Stage of PCT/JP03/016794 <div style="font-size: 1.5em; font-weight: bold;">10/538878</div>	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				APPLICANTS Masahiro SAKURADA et al.			
				FILING DATE June 14, 2005		GROUP	

U.S. PATENT DOCUMENTS						
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS

FOREIGN PATENT DOCUMENTS						
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS
	1	JP A 2000-351690 w/ abst & transl	12/19/2000	JAPAN		
	2	JP A 2000-178099 w/ abst & transl	6/27/2000	JAPAN		

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)		
	3	VORONKOV, "The Mechanism of Swirl Defects Formation in Silicon," <i>Journal of Crystal Growth</i> , vol. 59, no. 3, pp. 625-643 {March 1, 1982}
	4	DUPRET et al., "Global Modelling of Heat Transfer in Crystal Growth Furnaces," <i>Int. J. Heat Mass Transfer</i> , vol. 33, no. 9, pp. 1849-1871 {April 7, 1998}

EXAMINER	DATE CONSIDERED
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

Date: June 14, 2005